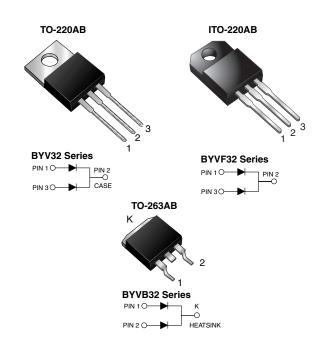


## BYV(F,B)32-50 thru BYV(F,B)32-200

Vishay General Semiconductor

### **Dual Common-Cathode Ultrafast Rectifier**



PRIMARY CHARACTERISTICS					
I <sub>F(AV)</sub>	18 A				
V <sub>RRM</sub>	50 V to 200 V				
I <sub>FSM</sub>	150 A				
t <sub>rr</sub>	25 ns				
V <sub>F</sub>	0.85 V				
T <sub>J</sub> max.	150 °C				

### **FEATURES**

- Glass passivated chip junction
- Ultrafast recovery time
- Low switching losses, high efficiency
- Low forward voltage drop
- High forward surge capability
- Meets MSL level 1, per J-STD-020, LF maximum peak of 245 °C (for TO-263AB package)
- Solder dip 260 °C, 40 s (for TO-220AB and ITO-220AB package)
- Component in accordance to RoHS 2002/95/EC and WEEE 2002/96/EC

#### **TYPICAL APPLICATIONS**

For use in high frequency rectifier of switching mode power supplies, inverters, freewheeling diodes, dc-to-dc converters, and other power switching application.

#### **MECHANICAL DATA**

Case: TO-220AB, ITO-220AB, TO-263AB

Epoxy meets UL 94V-0 flammability rating

Terminals: Matte tin plated leads, solderable per J-STD-002 and JESD22-B102

E3 suffix for consumer grade, meets JESD 201 class 1A whisker test, HE3 suffix for high reliability grade (AEC Q101 qualified), meets JESD 201 class 2 whisker test

Polarity: As marked

Mounting Torque: 10 in-lbs maximum

MAXIMUM RATINGS (T <sub>C</sub> = 25 °C unless otherwise noted)								
PARAMETER	SYMBOL	BYV32-50	BYV32-100	BYV32-150	BYV32-200	UNIT		
Maximum repetitive peak reverse voltage	V <sub>RRM</sub>	50	100	150	200	V		
Maximum RMS voltage	V <sub>RMS</sub>	35	70	105	140	V		
Maximum DC blocking voltage	V <sub>DC</sub>	V <sub>DC</sub> 50 100 150 200		200	V			
Maximum average forward rectified current at $T_C$ = 125 °C	I <sub>F(AV)</sub>	18				А		
Peak forward surge current 8.3 ms single half sine-wave superimposed on rated load per diode	I <sub>FSM</sub>	150				А		
Operating storage and temperature range	T <sub>J</sub> , T <sub>STG</sub>	- 65 to + 150 °C			°C			
Isolation voltage (ITO-220AB only) from terminal to heatsink t = 1 min	V <sub>AC</sub>	1500			V			

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<b>ELECTRICAL CHARACTERISTICS</b> ( $T_c = 25 \text{ °C}$ unless otherwise noted)								
PARAMETER	TEST CONDITIONS SYMBOL BYV32-50 BYV32-100 BYV32-150		BYV32-200	UNIT				
Maximum instantaneous forward voltage per diode <sup>(1)</sup>	I <sub>F</sub> = 20 A I <sub>F</sub> = 5.0 A	T <sub>J</sub> = 25 °C T <sub>J</sub> = 100 °C	V <sub>F</sub>	1.15 0.85				v
Maximum DC reverse current per diode at rated DC blocking voltage		T <sub>J</sub> = 25 °C T <sub>J</sub> = 100 °C	I <sub>R</sub>	10 600				μΑ
Maximum reverse recovery time per diode	$I_F = 1 \text{ A}, V_R = 1$ dl/dt = 100 A/µs		t <sub>rr</sub>	25			ns	
Typical junction capacitance per diode	4.0 V, 1 MHz		CJ	45			pF	

Note:

(1) Pulse test: 300 µs pulse width, 1 % duty cycle

<b>THERMAL CHARACTERISTICS</b> (T <sub>C</sub> = 25 °C unless otherwise noted)						
PARAMETER SYMBOL BYV BYVF BYVB U						
Typical thermal resistance from junction to case per diode	$R_{ ext{ heta}JC}$	1.6	5.0	1.6	°C/W	

ORDERING INFORMATION (Example)							
PACKAGE	PREFERRED P/N	UNIT WEIGHT (g)	PACKAGE CODE	BASE QUANTITY	DELIVERY MODE		
TO-220AB	BYV32-200-E3/45	1.85	45	50/tube	Tube		
ITO-220AB	BYVF32-200-E3/45	1.97	45	50/tube	Tube		
TO-263AB	BYVB32-200-E3/45	1.35	45	50/tube	Tube		
TO-263AB	BYVB32-200-E3/81	1.35	81	800/reel	Tape and reel		
TO-220AB	BYV32-200HE3/45 <sup>(1)</sup>	1.85	45	50/tube	Tube		
ITO-220AB	BYVF32-200HE3/45 <sup>(1)</sup>	1.97	45	50/tube	Tube		
TO-263AB	BYVB32-200HE3/45 <sup>(1)</sup>	1.35	45	50/tube	Tube		
TO-263AB	BYVB32-200HE3/81 <sup>(1)</sup>	1.35	81	800/reel	Tape and reel		

Note:

(1) Automotive grade AEC Q101 qualified



## BYV(F,B)32-50 thru BYV(F,B)32-200

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### **RATINGS AND CHARACTERISTICS CURVES**

(T<sub>A</sub> = 25 °C unless otherwise noted)

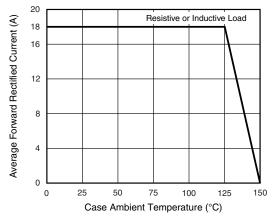


Figure 1. Forward Current Derating Curve

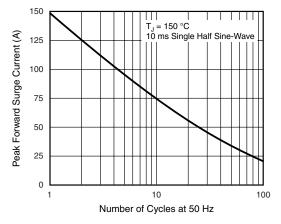


Figure 2. Maximum Non-Repetitive Peak Forward Surge Current Per Diode

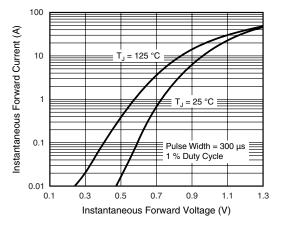


Figure 3. Typical Instantaneous Forward Characteristics Per Diode

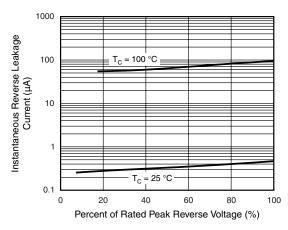


Figure 4. Typical Reverse Leakage Characteristics Per Diode

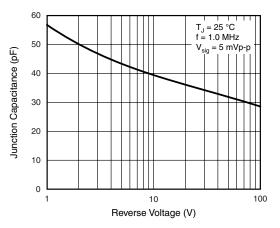
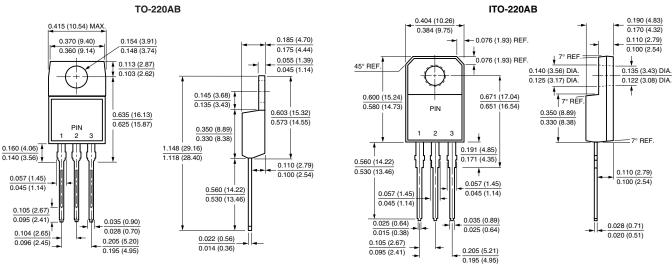


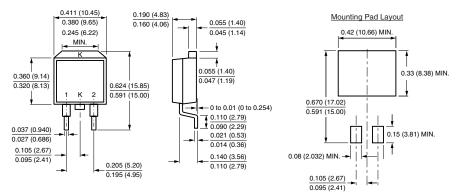
Figure 5. Typical Junction Capacitance Per Diode

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TO-263AB









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